

MOSFET

StrongIRFET™ 2 Power-Transistor

Features

- Optimized for a wide range of applications
- N-Channel, normal level
- 100% avalanche tested
- Pb-free lead plating; RoHS compliant
- Halogen-free according to IEC61249-2-21

Product validation

Qualified according to JEDEC Standard

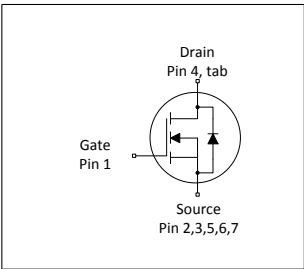
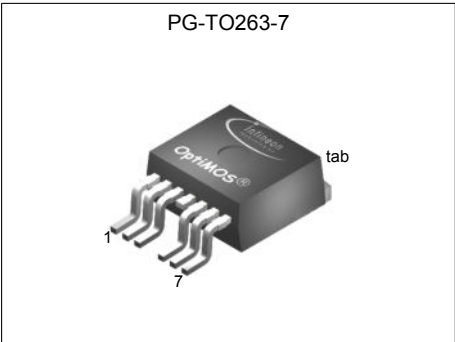


Table 1 Key Performance Parameters

Parameter	Value	Unit
V_{DS}	100	V
$R_{DS(on),max}$	4.25	$m\Omega$
I_D	139	A
Q_{oss}	74	nC
Q_G	57	nC

Type / Ordering Code	Package	Marking	Related Links
IPF042N10NF2S	PG-TO263-7	042N10NS	-

Table of Contents

Description 1

Maximum ratings 3

Thermal characteristics 3

Electrical characteristics 4

Electrical characteristics diagrams 6

Package Outlines 10

Revision History 11

Trademarks 11

Disclaimer 11

1 Maximum ratings

at $T_A=25\text{ °C}$, unless otherwise specified

Table 2 Maximum ratings

Parameter	Symbol	Values			Unit	Note / Test Condition
		Min.	Typ.	Max.		
Continuous drain current ¹⁾	I_D	-	-	139 98 88 21	A	$V_{GS}=10\text{ V}$, $T_C=25\text{ °C}$ $V_{GS}=10\text{ V}$, $T_C=100\text{ °C}$ $V_{GS}=6\text{ V}$, $T_C=100\text{ °C}$ $V_{GS}=10\text{ V}$, $T_A=25\text{ °C}$, $R_{thJA}=40\text{ °C/W}^{2)}$
Pulsed drain current ³⁾	$I_{D,pulse}$	-	-	556	A	$T_A=25\text{ °C}$
Avalanche energy, single pulse ⁴⁾	E_{AS}	-	-	105	mJ	$I_D=82\text{ A}$, $R_{GS}=25\text{ }\Omega$
Gate source voltage	V_{GS}	-20	-	20	V	-
Power dissipation	P_{tot}	-	-	167 3.8	W	$T_C=25\text{ °C}$ $T_A=25\text{ °C}$, $R_{thJA}=40\text{ °C/W}^{2)}$
Operating and storage temperature	T_j , T_{stg}	-55	-	175	°C	-

2 Thermal characteristics

Table 3 Thermal characteristics

Parameter	Symbol	Values			Unit	Note / Test Condition
		Min.	Typ.	Max.		
Thermal resistance, junction - case	R_{thJC}	-	-	0.9	°C/W	-
Thermal resistance, junction - ambient, 6 cm ² cooling area ²⁾	R_{thJA}	-	-	40	°C/W	-
Thermal resistance, junction - ambient, minimal footprint	R_{thJA}	-	-	62	°C/W	-

¹⁾ Rating refers to the product only with datasheet specified absolute maximum values, maintaining case temperature as specified. For other case temperatures please refer to Diagram 2. De-rating will be required based on the actual environmental conditions.

²⁾ Device on 40 mm x 40 mm x 1.5 mm epoxy PCB FR4 with 6 cm² (one layer, 70 µm thick) copper area for drain connection. PCB is vertical in still air.

³⁾ See Diagram 3 for more detailed information

⁴⁾ See Diagram 13 for more detailed information

3 Electrical characteristics

at $T_j=25\text{ °C}$, unless otherwise specified

Table 4 Static characteristics

Parameter	Symbol	Values			Unit	Note / Test Condition
		Min.	Typ.	Max.		
Drain-source breakdown voltage	$V_{(BR)DSS}$	100	-	-	V	$V_{GS}=0\text{ V}$, $I_D=1\text{ mA}$
Gate threshold voltage	$V_{GS(th)}$	2.2	3.0	3.8	V	$V_{DS}=V_{GS}$, $I_D=93\text{ }\mu\text{A}$
Zero gate voltage drain current	I_{DSS}	-	0.1 10	1 100	μA	$V_{DS}=100\text{ V}$, $V_{GS}=0\text{ V}$, $T_j=25\text{ °C}$ $V_{DS}=100\text{ V}$, $V_{GS}=0\text{ V}$, $T_j=125\text{ °C}$
Gate-source leakage current	I_{GSS}	-	10	100	nA	$V_{GS}=20\text{ V}$, $V_{DS}=0\text{ V}$
Drain-source on-state resistance	$R_{DS(on)}$	-	3.7 4.5	4.25 5.3	m Ω	$V_{GS}=10\text{ V}$, $I_D=80\text{ A}$ $V_{GS}=6\text{ V}$, $I_D=40\text{ A}$
Gate resistance	R_G	-	1.3	-	Ω	-
Transconductance ¹⁾	g_{fs}	71	-	-	S	$ V_{DS} \geq 2 I_D /R_{DS(on)max}$, $I_D=80\text{ A}$

Table 5 Dynamic characteristics

Parameter	Symbol	Values			Unit	Note / Test Condition
		Min.	Typ.	Max.		
Input capacitance	C_{iss}	-	4000	-	pF	$V_{GS}=0\text{ V}$, $V_{DS}=50\text{ V}$, $f=1\text{ MHz}$
Output capacitance	C_{oss}	-	630	-	pF	$V_{GS}=0\text{ V}$, $V_{DS}=50\text{ V}$, $f=1\text{ MHz}$
Reverse transfer capacitance	C_{rss}	-	28	-	pF	$V_{GS}=0\text{ V}$, $V_{DS}=50\text{ V}$, $f=1\text{ MHz}$
Turn-on delay time	$t_{d(on)}$	-	18	-	ns	$V_{DD}=50\text{ V}$, $V_{GS}=10\text{ V}$, $I_D=80\text{ A}$, $R_{G,ext}=1.6\text{ }\Omega$
Rise time	t_r	-	71	-	ns	$V_{DD}=50\text{ V}$, $V_{GS}=10\text{ V}$, $I_D=80\text{ A}$, $R_{G,ext}=1.6\text{ }\Omega$
Turn-off delay time	$t_{d(off)}$	-	27	-	ns	$V_{DD}=50\text{ V}$, $V_{GS}=10\text{ V}$, $I_D=80\text{ A}$, $R_{G,ext}=1.6\text{ }\Omega$
Fall time	t_f	-	8	-	ns	$V_{DD}=50\text{ V}$, $V_{GS}=10\text{ V}$, $I_D=80\text{ A}$, $R_{G,ext}=1.6\text{ }\Omega$

Table 6 Gate charge characteristics²⁾

Parameter	Symbol	Values			Unit	Note / Test Condition
		Min.	Typ.	Max.		
Gate to source charge	Q_{gs}	-	19	-	nC	$V_{DD}=50\text{ V}$, $I_D=80\text{ A}$, $V_{GS}=0\text{ to }10\text{ V}$
Gate charge at threshold	$Q_{g(th)}$	-	12	-	nC	$V_{DD}=50\text{ V}$, $I_D=80\text{ A}$, $V_{GS}=0\text{ to }10\text{ V}$
Gate to drain charge	Q_{gd}	-	12	-	nC	$V_{DD}=50\text{ V}$, $I_D=80\text{ A}$, $V_{GS}=0\text{ to }10\text{ V}$
Switching charge	Q_{sw}	-	19	-	nC	$V_{DD}=50\text{ V}$, $I_D=80\text{ A}$, $V_{GS}=0\text{ to }10\text{ V}$
Gate charge total ¹⁾	Q_g	-	57	85	nC	$V_{DD}=50\text{ V}$, $I_D=80\text{ A}$, $V_{GS}=0\text{ to }10\text{ V}$
Gate plateau voltage	$V_{plateau}$	-	4.8	-	V	$V_{DD}=50\text{ V}$, $I_D=80\text{ A}$, $V_{GS}=0\text{ to }10\text{ V}$
Gate charge total, sync. FET	$Q_{g(sync)}$	-	49	-	nC	$V_{DS}=0.1\text{ V}$, $V_{GS}=0\text{ to }10\text{ V}$
Output charge	Q_{oss}	-	74	-	nC	$V_{DS}=50\text{ V}$, $V_{GS}=0\text{ V}$

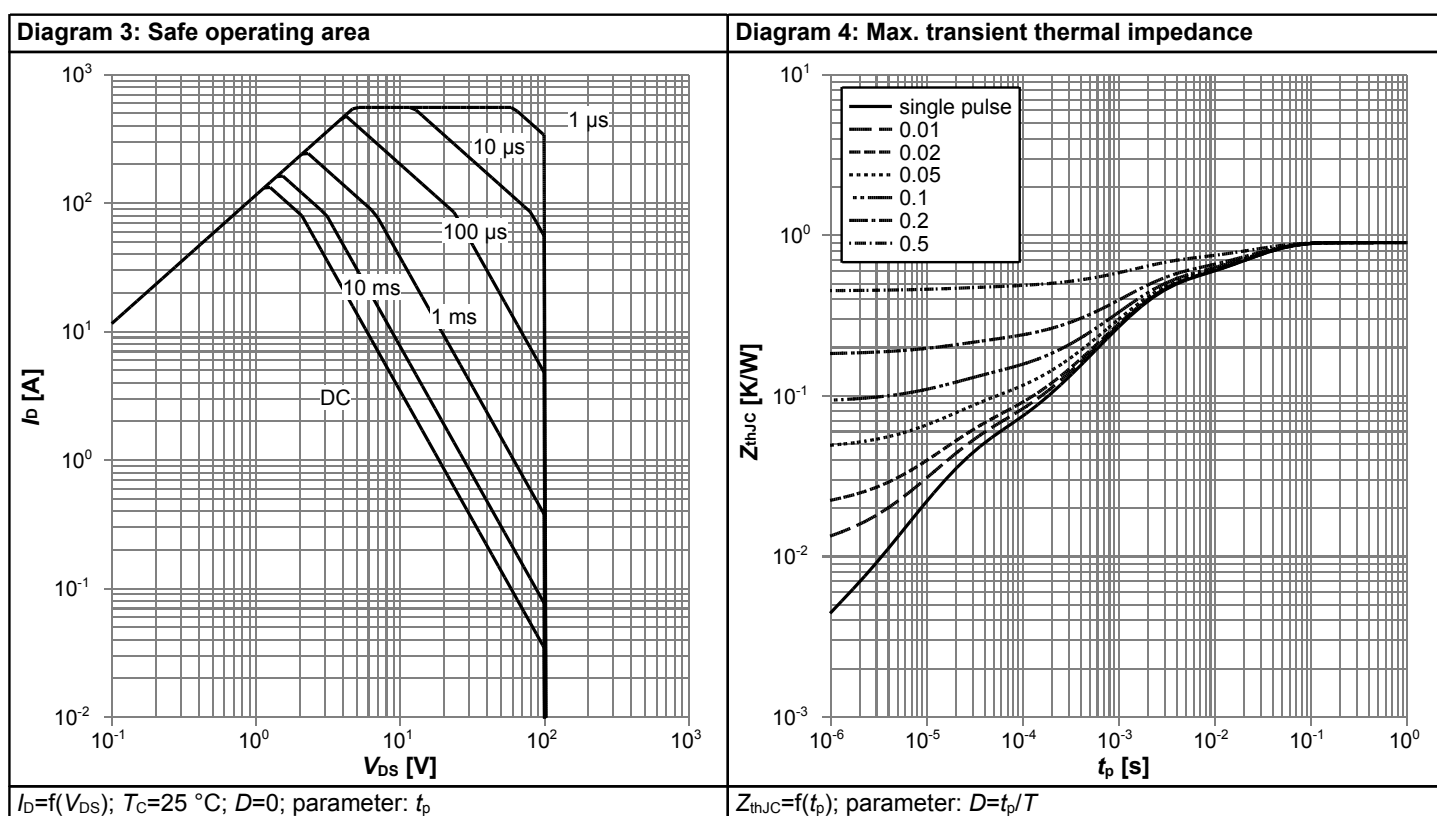
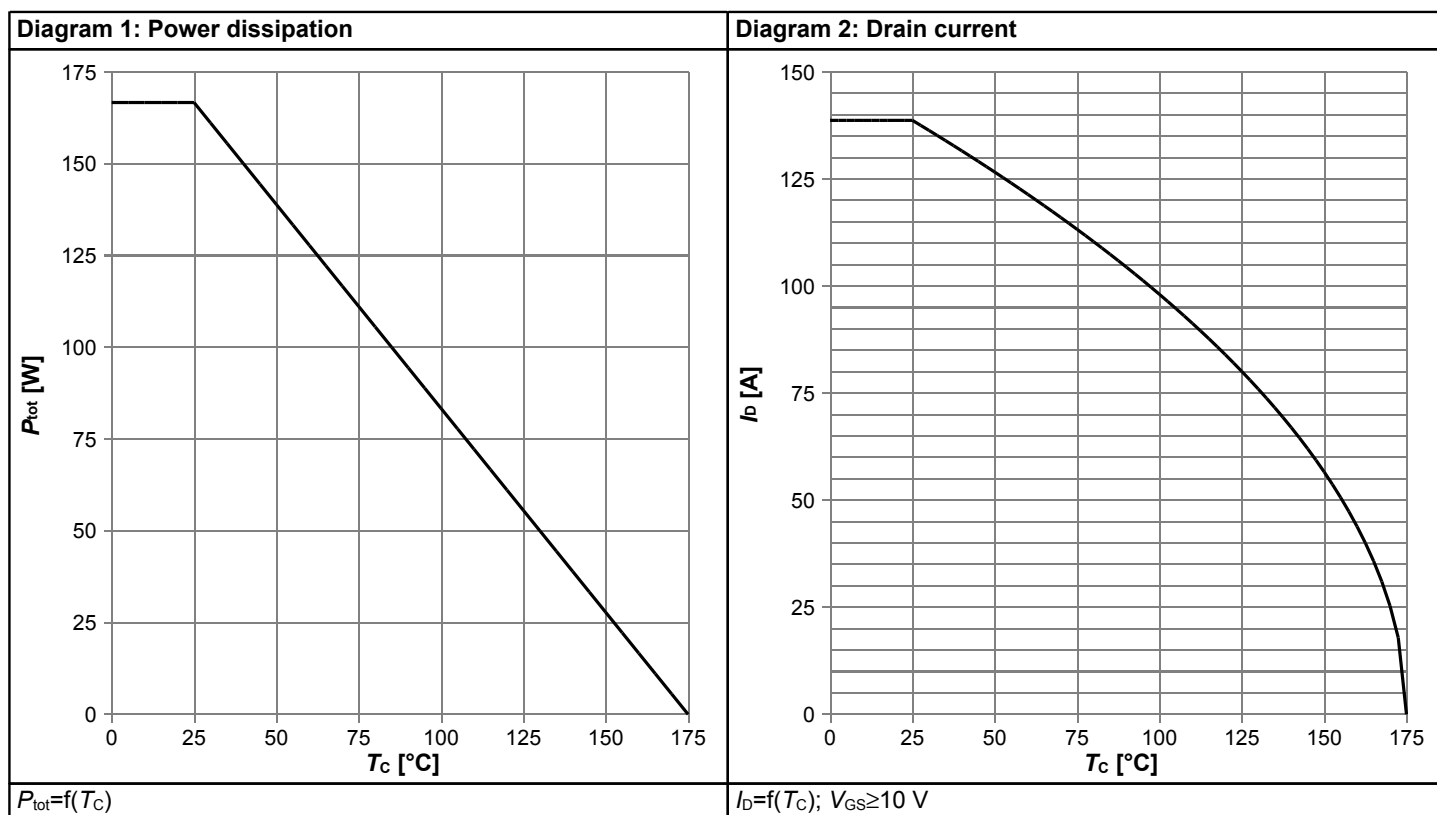
¹⁾ Defined by design. Not subject to production test.

²⁾ See "Gate charge waveforms" for parameter definition

Table 7 Reverse diode

Parameter	Symbol	Values			Unit	Note / Test Condition
		Min.	Typ.	Max.		
Diode continuous forward current	I_S	-	-	123	A	$T_C=25\text{ °C}$
Diode pulse current	$I_{S,pulse}$	-	-	556	A	$T_C=25\text{ °C}$
Diode forward voltage	V_{SD}	-	0.91	1.2	V	$V_{GS}=0\text{ V}$, $I_F=80\text{ A}$, $T_j=25\text{ °C}$
Reverse recovery time	t_{rr}	-	40	-	ns	$V_R=50\text{ V}$, $I_F=80\text{ A}$, $di_F/dt=500\text{ A}/\mu\text{s}$
Reverse recovery charge	Q_{rr}	-	287	-	nC	$V_R=50\text{ V}$, $I_F=80\text{ A}$, $di_F/dt=500\text{ A}/\mu\text{s}$

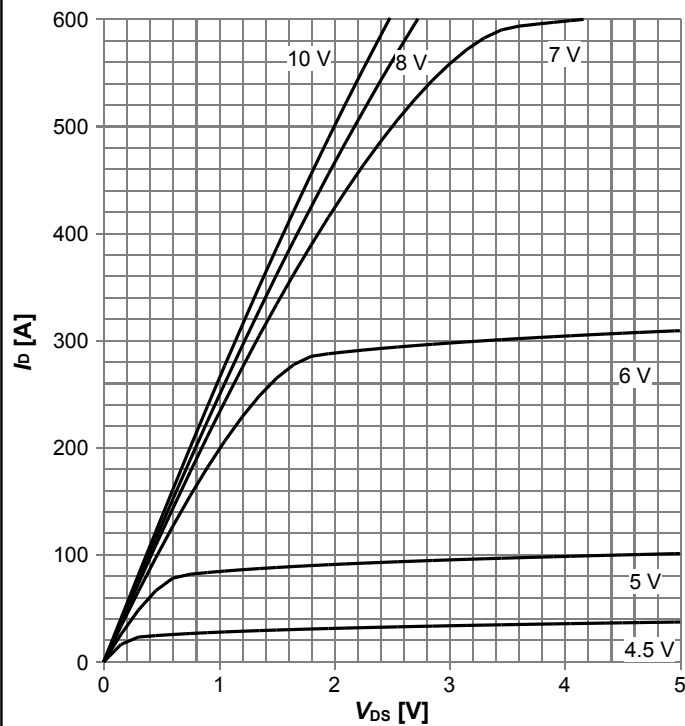
4 Electrical characteristics diagrams



StrongIRFET™ 2 Power-Transistor

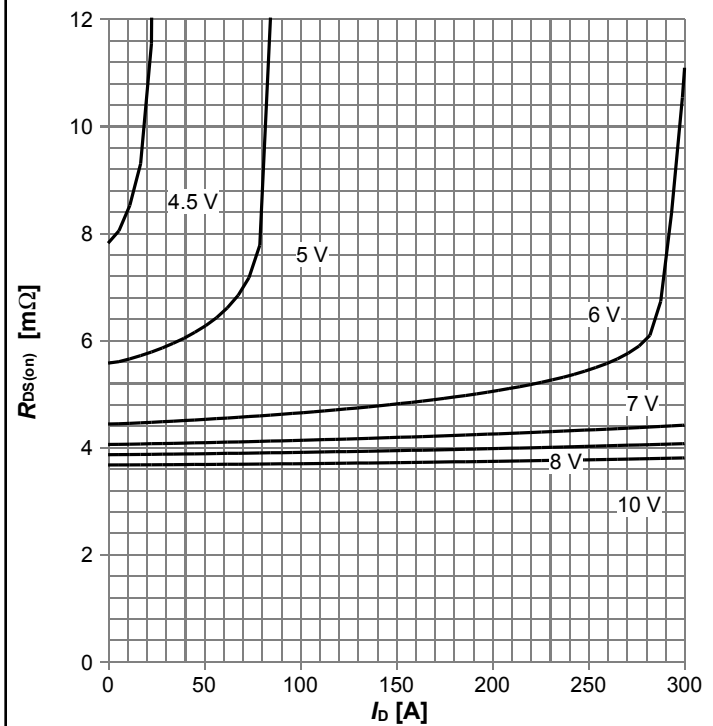
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Diagram 5: Typ. output characteristics



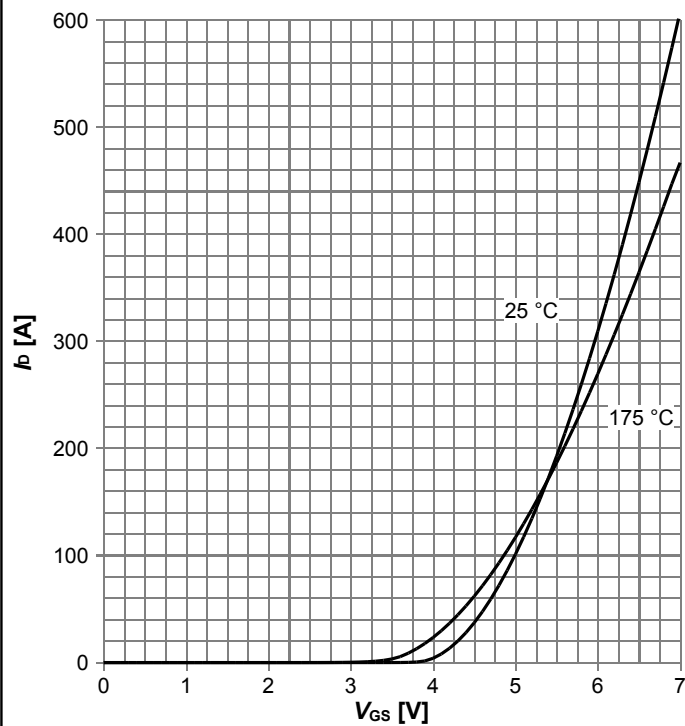
$I_D = f(V_{DS})$, $T_j = 25^\circ\text{C}$; parameter: V_{GS}

Diagram 6: Typ. drain-source on resistance



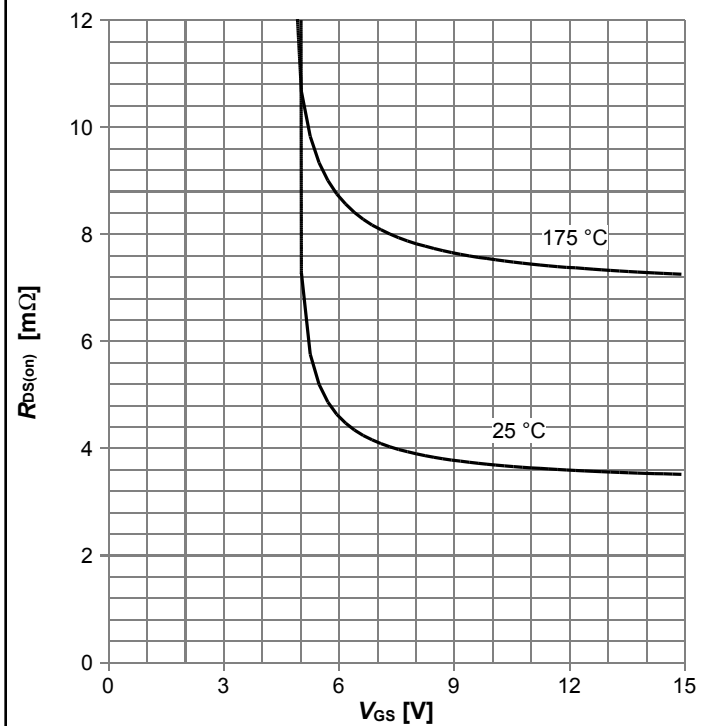
$R_{DS(on)} = f(I_D)$, $T_j = 25^\circ\text{C}$; parameter: V_{GS}

Diagram 7: Typ. transfer characteristics



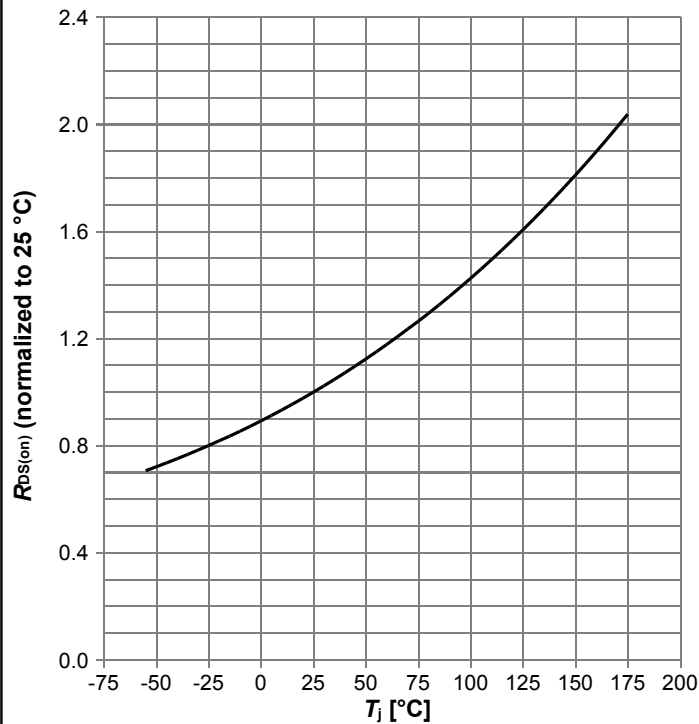
$I_D = f(V_{GS})$, $|V_{DS}| > 2|I_D|R_{DS(on)max}$; parameter: T_j

Diagram 8: Typ. drain-source on resistance



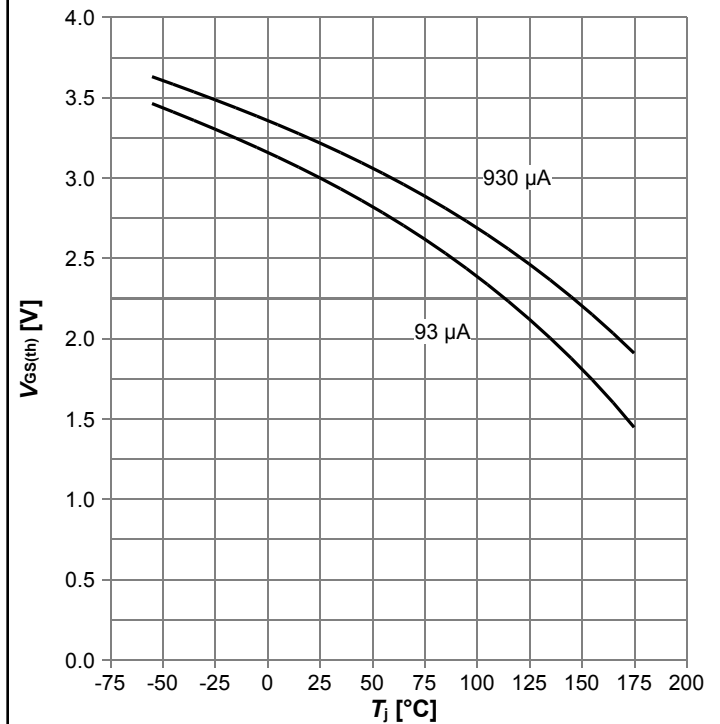
$R_{DS(on)} = f(V_{GS})$, $I_D = 80\text{ A}$; parameter: T_j

Diagram 9: Normalized drain-source on resistance



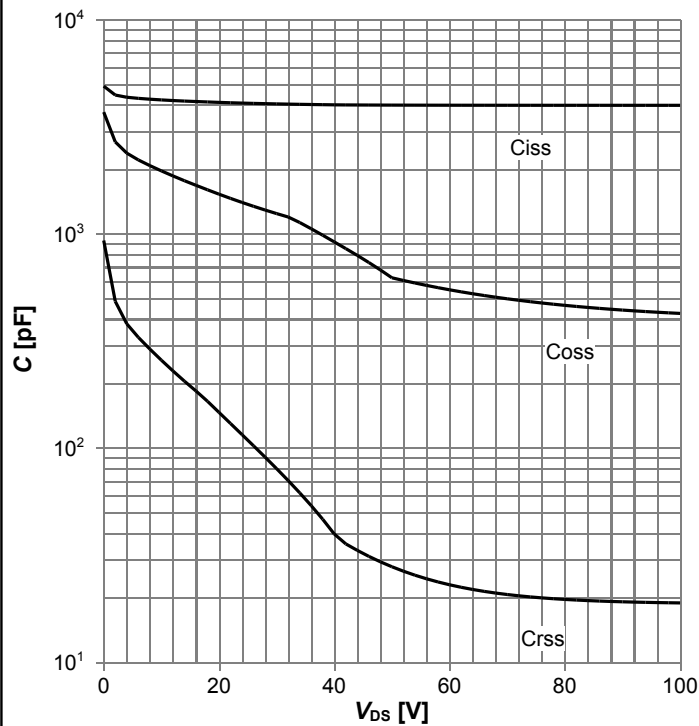
$R_{DS(on)} = f(T_j)$, $I_D = 80$ A, $V_{GS} = 10$ V

Diagram 10: Typ. gate threshold voltage



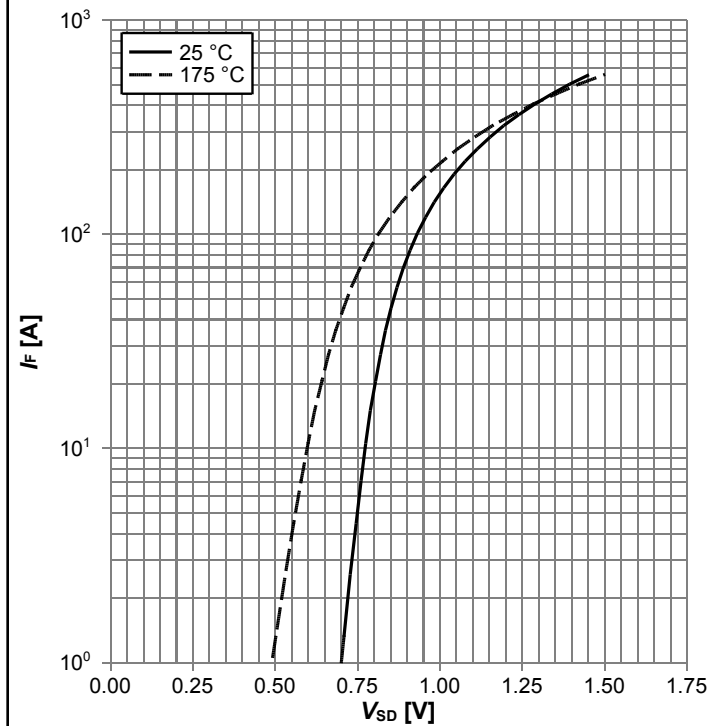
$V_{GS(th)} = f(T_j)$, $V_{GS} = V_{DS}$; parameter: I_D

Diagram 11: Typ. capacitances



$C = f(V_{DS})$; $V_{GS} = 0$ V; $f = 1$ MHz

Diagram 12: Typ. forward characteristics of reverse diode

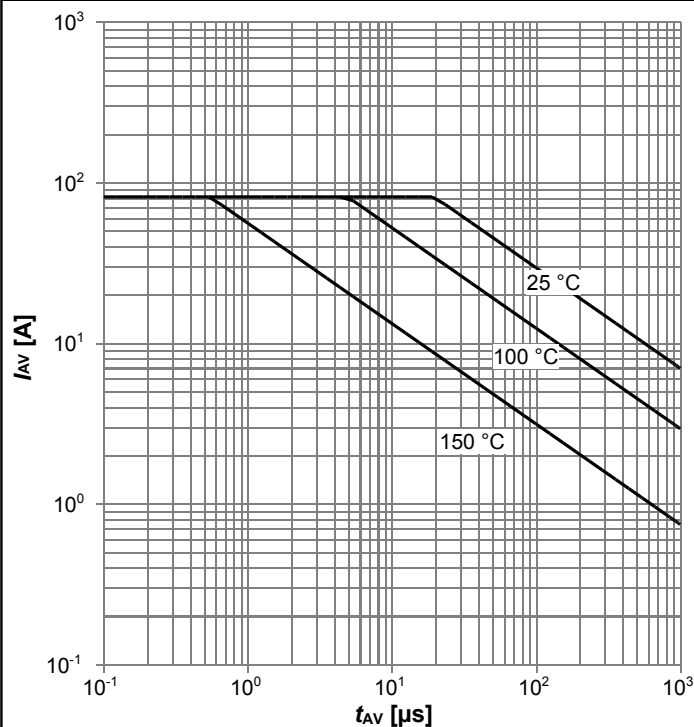


$I_F = f(V_{SD})$; parameter: T_j

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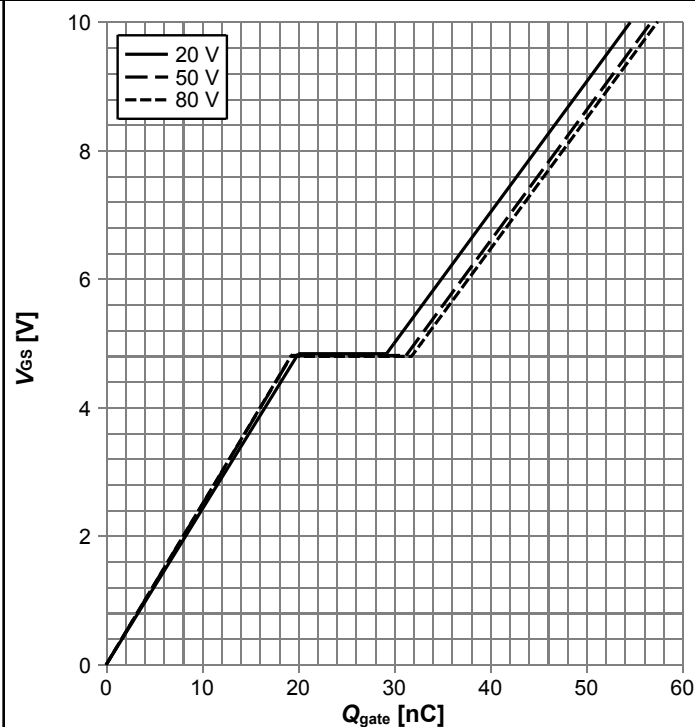
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Diagram 13: Avalanche characteristics



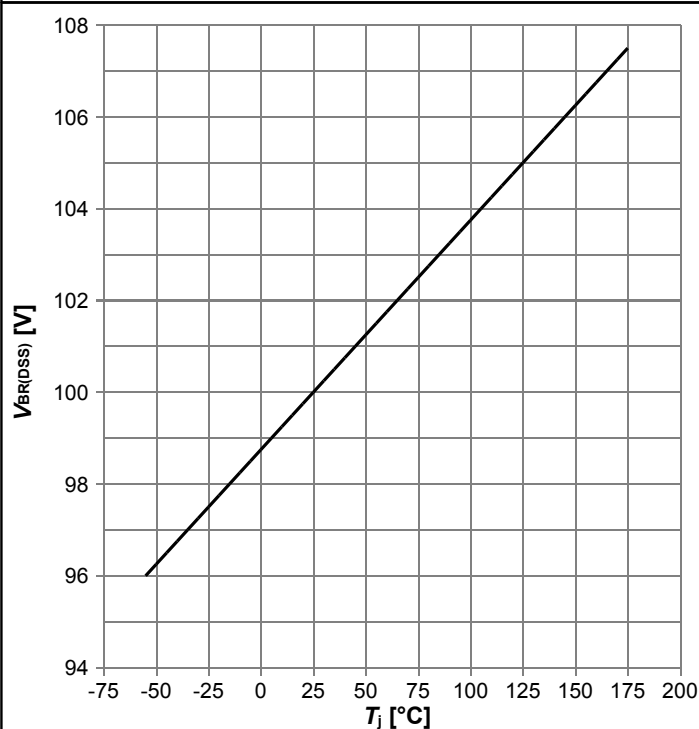
$I_{AS}=f(t_{AV})$; $R_{GS}=25\ \Omega$; parameter: $T_{j,start}$

Diagram 14: Typ. gate charge



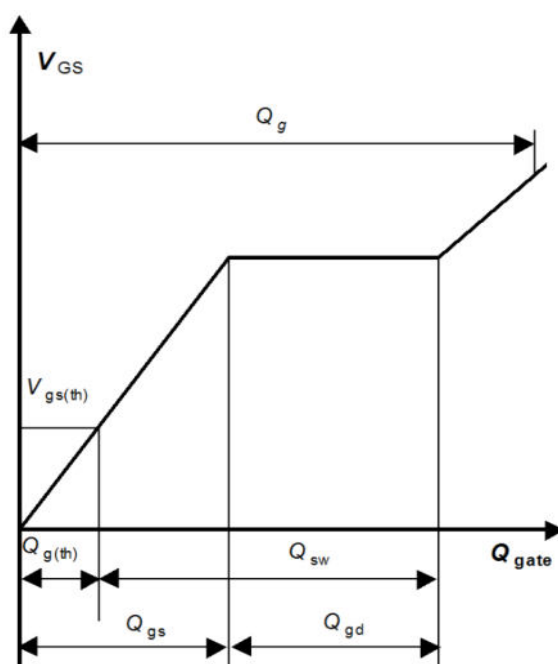
$V_{GS}=f(Q_{gate})$, $I_D=80\text{ A}$ pulsed, $T_j=25\text{ °C}$; parameter: V_{DD}

Diagram 15: Drain-source breakdown voltage

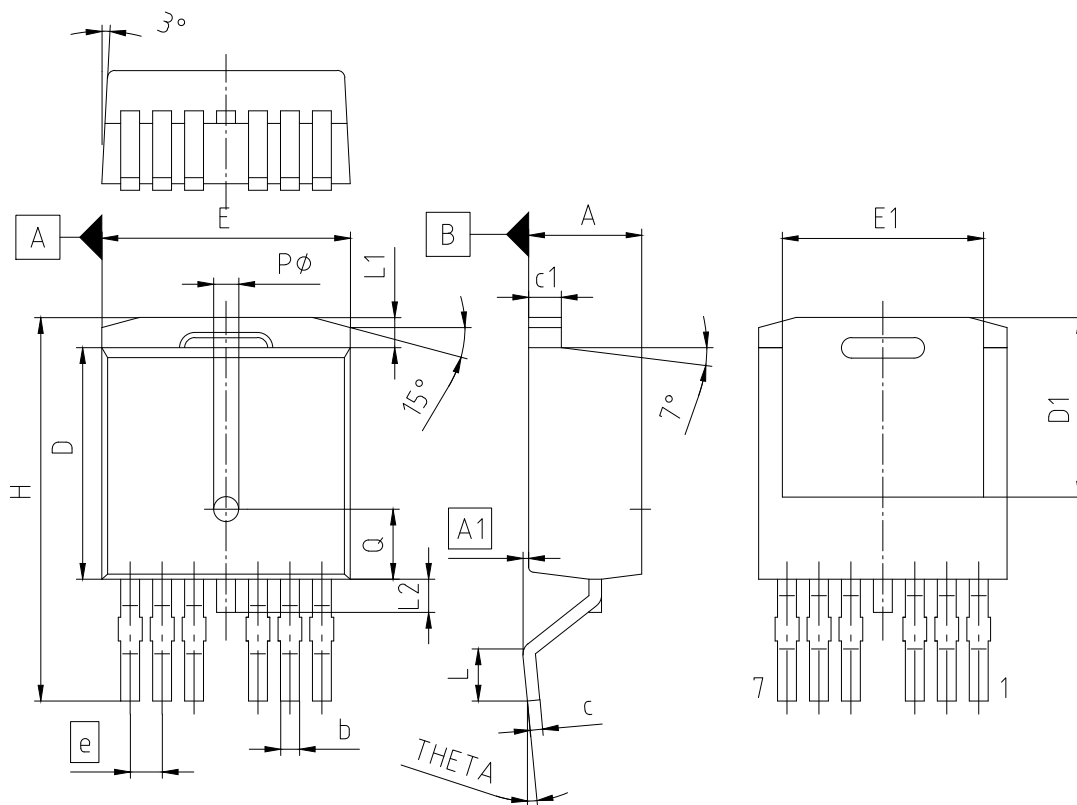


$V_{BR(DSS)}=f(T_j)$; $I_D=1\text{ mA}$

Diagram Gate charge waveforms



5 Package Outlines



PACKAGE - GROUP NUMBER: PG-TO263-7-U02		
DIMENSIONS	MILLIMETERS	
	MIN.	MAX.
A	4.30	4.70
A1	0.00	0.25
b	0.65	0.85
c	0.45	0.60
c1	1.25	1.40
D	9.00	9.40
D1	6.86	7.42
E	9.68	10.08
E1	7.70	8.30
e	1.27	
N	7	
H	14.61	15.88
L	1.78	2.79
L1	0.00	1.60
L2	0.00	1.78
THETA	0° - 8°	
PØ	0.90	1.10
Q	2.78	

Figure 1 Outline PG-TO263-7, dimensions in mm

Revision History

IPF042N10NF2S

Revision: 2022-09-23, Rev. 2.0

Previous Revision

Revision	Date	Subjects (major changes since last revision)
2.0	2022-09-23	Release of final version

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Published by

Infineon Technologies AG

81726 München, Germany

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